

USSN 09/910,795
Art Unit: 1765

Amendments to the Specification

Please amend the paragraph commencing at line 5, page 7 as follows:

— Next, in step 4 a sacrificial layer 22 of CRPVD TiN about 0.10 μm thick is deposited at 400°C. In step 5, a layer 24 of PECVD Si_3N_4 about 0.40 μm thick is deposited at 400°C. In step 6, a sacrificial layer 26 of CRPVD TiN about 0.20 μm thick is deposited at 400°C. --

Please amend the paragraph commencing at line 21, page 7 as follows:

— In step 9, shown in Figure 4, a layer of CRPVD TiN 30 about 0.10 μm thick is deposited at 400°C. --